

1N6840 AND 1N6841

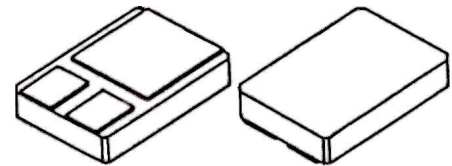
DESIGNER'S DATA SHEET

FEATURES:

- Low Profile Ceramic SMD
- High Surge Rating
- Low Reverse Leakage Current
- Low Forward Voltage
- Seam Welded Package
- Low Capacitance
- Ultrasonic Aluminum Wire Bonds

35 and 45 VOLTS, 10 AMP
 DUAL SCHOTTKY
 COMMON CATHODE
 CENTERTAP RECTIFIER

SMD-0.5



MAXIMUM RATINGS (per leg)

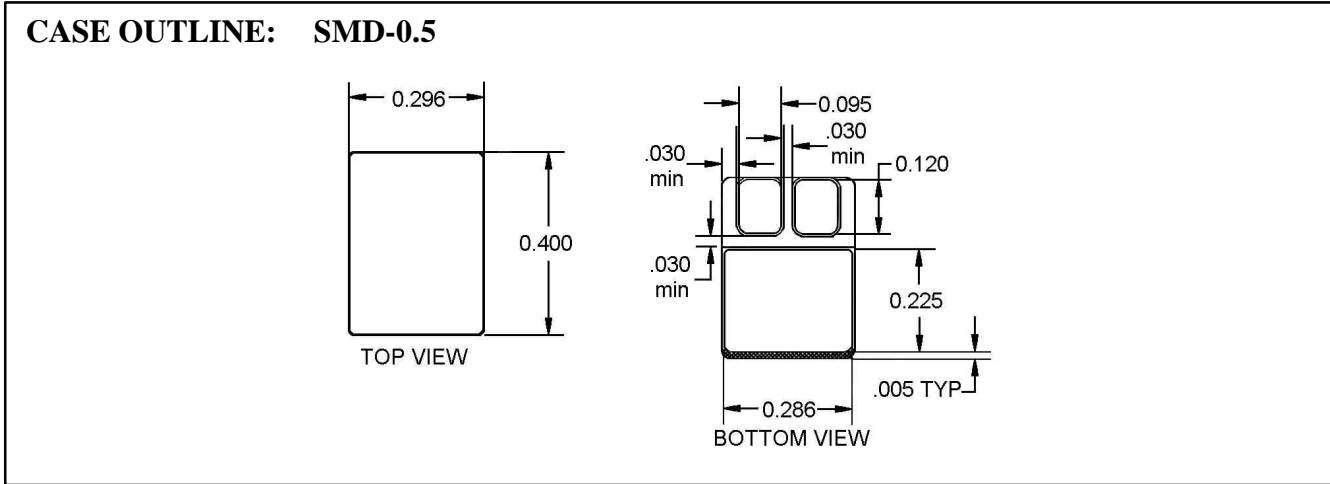
RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse and DC Blocking Voltage 1N6840 1N6841	V_{RRM} V_{RWN} V_R	 35 45	 Volts
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, TA = 25°C)	I_o	10	Amps
Peak Surge Current (8.3 ms Pulse, TA = 25°C, per leg)	I_{FSM}	200	Amps
Operating & Storage Temperature	Top & Tstg	-55 to +150	°C
Maximum Thermal Resistance Junction to Case, each individual diode Junction to Case <i>Note 1</i>	$R_{\theta JC}$	2.8 1.7	°C/W

Note 1: Both legs tied together
 8/2/99

1N6840 AND 1N6841

ELECTRICAL CHARACTERISTICS (per leg)

CHARACTERISTICS	SYMBOL	MAX.	UNIT
Instantaneous Forward Voltage Drop ($I_F = 3 \text{ Adc}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse) ($I_F = 10 \text{ Adc}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse) ($I_F = 20 \text{ Adc}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse)	V_F	0.62 0.75 0.88	Vdc
Instantaneous Forward Voltage Drop ($I_F = 10 \text{ Adc}$, $T_A = 100^\circ\text{C}$, 300 μs Pulse) ($I_F = 20 \text{ Adc}$, $T_A = 100^\circ\text{C}$, 300 μs Pulse)	V_F	0.63 0.70	Vdc
Reverse Leakage Current (Rated V_R , $T_A = 25^\circ\text{C}$, 300 μs pulse minimum)	I_R	100	μA
Reverse Leakage Current (Rated V_R , $T_A = 100^\circ\text{C}$, 300 μs pulse minimum)	I_R	10	mA
Junction Capacitance $V_R = 10\text{Vdc}$, $T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$)	C_J	400	Pf



TYPICAL OPERATING CURVES
 ($T_A = 25^\circ\text{C}$ Unless otherwise specified)

